

Shottky barrier diode

(Silicon Epitaxial Planer)

RB480Y

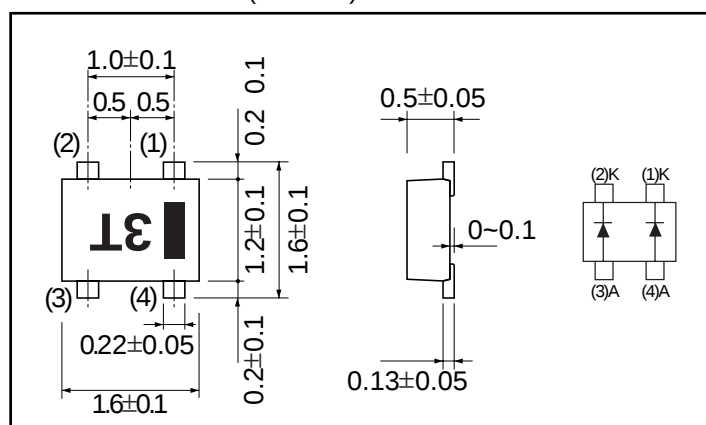
●Applications

Rectifying small power

●Features

- 1) Ultra small mold type (EMD4)
- 2) High reliability

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage	V_R	30	V
Average rectified forward current *	I_o	100	A
Forward current surge peak (60Hz · 1cyc.) *	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

*60Hz for 1 $\varnothing$

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	—	0.38	V	$I_F=1mA$
	V_{F2}	—	—	0.430	V	$I_F=10mA$
	V_{F3}	—	—	0.530	V	$I_F=100mA$
Reverse current	I_R	—	—	1.0	μA	$V_R=10V$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

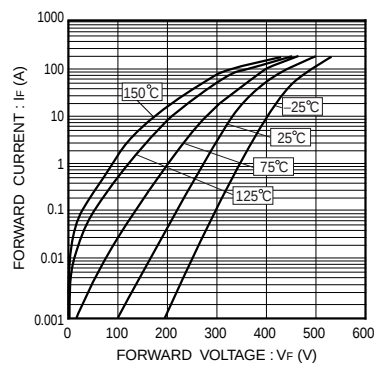


Fig.1 Forward temperature characteristics

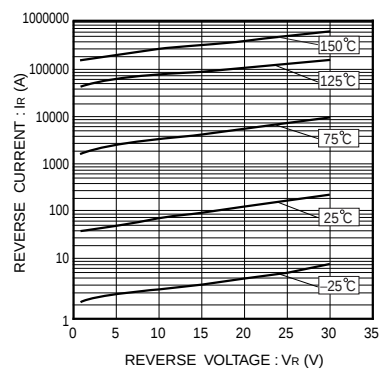


Fig.2 Reverse temperature characteristics

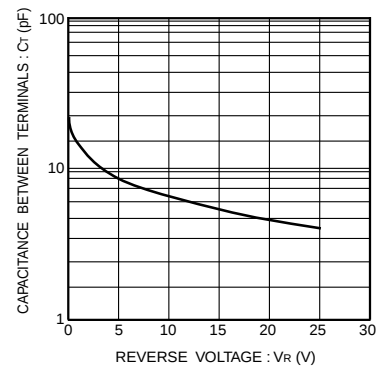


Fig.3 Capacitance between terminals characteristics